

SILICON HYPERABRUPT TUNING DIODES

- High capacitance ratios
- Linear tuning between 2 and 8 volts
- Available over a broad range junction capacitances
- Satisfies a large number of broadband applications thru the VHF frequency band

KSV1401 - KSV1412

PART NUMBER	DIODE CAPACITANCE (CT)				TUNING RATIO (TR) C•1V / C•10V C•2V / C•10V		QUALITY FACTOR Q @ 2V • 1 MHz MIN
	pF @ 1V•1 MHz MIN	pF @ 1V•1 MHz MAX	pF @ 2V•1 MHz MIN	pF @ 2V•1 MHz MAX	@ 1 MHz MIN	@ 1 MHz MIN	
KSV1401	440	660			14:1		200
KSV1402			45	69		10:1	200
KSV1403			140	210		10:1	200
KSV1404			96	144		10:1	200
KSV1405			200	300		10:1	200
KSV1406			80	120		10:1	200
KSV1407			54	82		10:1	200
KSV1408			37	57		10:1	200
KSV1409			26	40		10:1	200
KSV1410			17	27		9.5:1	200
KSV1411			12	18		8.5:1	200
KSV1412			8	12		7.5:1	200

Package Style

Device Dissipation (Pd)

Junction Temperature (Tj)

Reverse Breakdown Voltage (VBR)

Max Reverse Leakage Current (Ir)

Operating Temperature (Topr)

Storage Temperature (Tstg)

Capacitance Tolerance

TA = 25°C

10 µAdc

Vr = 10 Vdc

Standard Device

Suffix A

Suffix B

DO-7

400 mW

175°C

12 Vdc Min

0.1 µAdc

-55° to + 150°C

-65° to + 200°C

± 20%

± 10%

± 5%

To order devices screened to MIL-PRF-19500 JANTX level, Appendix E, Table IV add suffix H.